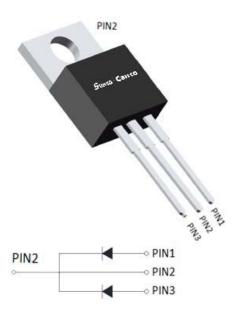


# **Schottky Diodes**



### **Features**

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

#### **Typical Applications**

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

#### **Mechanical Data**

• Package: TO-220AB

Molding compound meets UL 94 V-0 flammability rating -

rating, -

• **Terminals**: Tin plated leads, solderable per J-STD-002 and JESD22-B102

Polarity: As marked

#### ■Maximum Ratings (Ta=25°C Unless otherwise specified)

= maximum Natings (1a 25 6 cm est of mest opening)					
PARAMETER	SYMBOL	UNIT	MBR3060CT		
Device marking code			MBR3060CT		
Repetitive Peak Reverse Voltage	VRRM	V	60		
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25℃	lo	Α	30		
Surge(Non-repetitive)Forward Current @60H <sub>Z</sub> half sine-wave,1 cycle, T <sub>a</sub> =25℃	IFSM	Α	250		
Current Squared Time @1ms≤t≤8.3ms Tj=25℃,	l²t	A <sup>2</sup> s	260		
Storage Temperature	T <sub>stg</sub>	°C	-55 ~ +150		
Junction Temperature Tj		$^{\circ}$	-55 ~ <b>+</b> 150		

### **■Electrical Characteristics** (T<sub>a</sub>=25°C Unless otherwise specified)

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PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR3060CT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=15.0A	0.72
Maximum DC reverse current at rated DC blocking voltage per- diode	IRRM1	mA ·	VRM=VRRM T <sub>a</sub> =25℃	0.2
	IRRM2		VRM=VRRM T <sub>a</sub> =125℃	50



# 

PARAMETER		SYMBOL	UNIT	MBR3060CT
Thermal Resistance	Between junction and case	R <sub>θJ-C</sub>	°C <b>/W</b>	2.0

**■Ordering Information** (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR3060CT	Approximate 1.9	50	1000	5000	Tube

# **■Characteristics** (Typical)

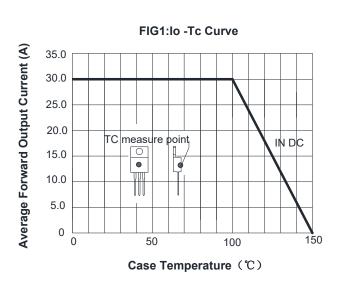
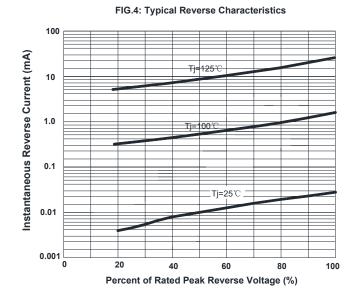


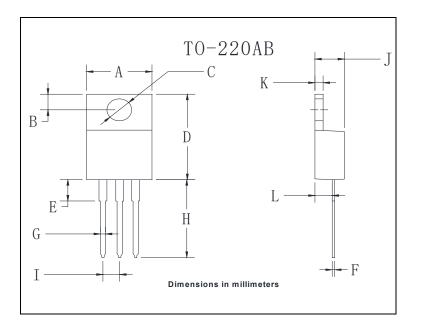
FIG2:Surge Forward Current Capability 300 Peak Forward Surge Current (A) 250 200 8.3ms Single Half Sine-Wave 150 JEDEC Method 100 50 0 2 5 20 10 50 100 **Number of Cycles** 

FIG3: Forward Voltage 100 60 Instantaneous Forward Current (A) 20 10 5.0 1.0 0.5 0.2 Ta=25℃ 0.1 0 0.6 0.7 0.9 0.8 0.4 0.5 Instantaneous Forward Voltage (V)





### **■**Outline Dimensions



TO-220AB				
Dim	Min	Max		
Α	9.5	10.9		
В	2.22	3.27		
С	3.34	4.31		
D	14.5	15.5		
Е	3.16	4.46		
F	0.28	0.64		
G	0.68	0.94		
Н	13.06	14.62		
1	2.01	3.07		
J	4.04	5.1		
K	1.14	1.4		
L	2.14	3.19		



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